

# George Stavrinidis

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## Personal Details

**Born** in Heraklion, Greece 12 November 1983  
**Nationality:** Greek  
**Marital status:** Married  
**Military obligations:** Completed

## Working address:

Microelectronics Research Group (MRG)  
Institute of Electronic Structure and Laser (IESL)  
Foundation for Research and Technology (FORTH)  
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## Education

July 2009 **B.Sc** in Electronics engineering, Technical Institute of Crete, Heraklion, Greece  
**Thesis:** "Design and fabrication of automatic system for selection of telephony services providers"  
2009 Certificate for good knowledge of Computing from the Technical Institute of Crete, Greece

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## Microelectronics processing skills

### Microelectronics processing

Lithography – UV, DUV (Karl Suss MA6 & MJB3 Mask aligner)  
Plasma reactive Ion etching (Chlorine and Fluorine based chemistries)  
Rapid thermal annealing (RTA for contact activation)  
Chemical treatment, chemical preparation

### 2D materials

Transfer of 2D materials to arbitrary substrates  
Electrical contacts including material pre and post treatment, for contact activation  
Fabrication of FETs  
Encapsulation using PECVD and ALD layer optimized for 2D materials  
Process development and optimization

### III-V Semiconductors

Electrical Contacts with Rapid Thermal Annealing  
Wet etching  
Reactive ion etching techniques  
Fabrication of FETs, HEMTS, PHEMTS  
Fabrication of III-V MMICs

### Wide Band Gap Semiconductors:

Electrical Contacts for SiC and III-Nitrides,  
Reactive Ion Etching of SiC and III-Nitrides,  
Fabrication of III-N MMICs  
Fabrication of GaN devices (HEMTs, Sensors)

### MicroElectroMechanical Systems (MEMS)

Biomedical devices  
High frequency circuits on thin membranes (RF MEMS)  
RF Switches  
Micromachining of compound semiconductor SAW and FBAR for chemical, thermal and humidity sensors

**Work experience**

2009 – today

- **Process engineer**

- FORTH – IESL, Microelectronics Research Group, Irakleio, Greece
  - Processing of Graphene and other 2D materials
  - Processing of III-Nitrides for RF power electronics,
  - Processing of III-Arsenides for optoelectornics
  - Processing of Micro Electro Mechanical Systems

**Participation in research projects**

- JU ENIAC call 1 “Introduction to experimental Physics”
  - SE2A – Nanoelectronics for Safe, Fuel Efficient and Environment Friendly Automotive Solutions
- FP7
  - NANORF - Carbon Based Smart Systems For wireless applications
  - NANOTEC – Nanostructured materials and RF-MEMS RFIC/MMIC technologies for highly adaptive and reliable RF systems
  - SMARTPOWER - Smart integration of GaN & SiC high power electronics for industrial and RF applications
- ENIAC
  - NANOCOM – Micro and Nano Technologies Based on Wide Band Gap Materials for Future Transmitting Receiving and Sensing Systems
  - MERCURE - Micro- and nanotechnologies based on wide band gap materials for future communication and sensing systems
- Cooperation between Greece and Russia
  - EINSTEIN PROJECT
- REASEARCH CREATE INOVATE
  - RADAR
- H2020
  - CHIRON

**Languages \***

\*(Common European Framework of Reference for Languages)

	Understanding		Speaking		Writing
	Listening	Reading	Spoken Interaction	Spoken production	
<b>Greek</b>	Native speaker				
<b>English</b>	Independent user (B2)	Proficient user (B2)	Proficient user (B2)	Proficient user (B2)	Independent user (B2)

**Publications summary**

	<i>Publications record</i>	<i>Impact</i>	
Published articles in journals & conferences:	23	Citations	210
		h-index	6

<https://www.scopus.com/authid/detail.uri?authorId=43762348700>